CLAIM AMENDMENTS

1. (original) A method for manufacturing an on-chip inductor consisting of:

creating at least one dielectric layer;

creating at least one conductive winding on the at least one dielectric layer; and

creating a P-well having a major surface parallel to a major surface of the dielectric layer.

2. (original) The method of claim 1 further consists of:

creating a field oxide having a major surface that is juxtaposed to the major surface of the P-well.

3. (original) The method of claim 1 further consists of:

creating the at least one dielectric layer to include one layer; and

creating the at least one conductive winding to include a spiral winding on the one layer.

4. (Currently amended) The method of claim 1 further consists of:

creating the at least one dielectric layer to include a plurality of layers; and

creating the at least <u>one</u> conductive winding to include a plurality of single windings <u>on</u> <u>one</u> the plurality of layers.

5. (original) The method of claim 1 further consists of:

creating the at least one dielectric layer to include a plurality of layers; and

creating the at least conductive winding to include a plurality of spiral windings one the plurality of layers.

6. (original) The method of claim 1 further consists of:

creating a substrate having a major surface parallel to the major surface of the at least one dielectric layer.

7. (original) The method of claim 1 further consists of:

creating a secondary winding magnetically coupled to the conductive winding.

8. (original) The method of claim 1, wherein the at least one conductive winding further consists of:

creating a center tap operably coupled to a reference potential to produce a differential inductor.

9-15 (cancelled)